









CEB170N10S

100V ▲ 3.1mΩ ▲ 168A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type

N-channel enhancement mode

UL94V-0 rated flame retardant epoxy

TO263 (D2PAK) package ▲ MSL 3

Super high dense cell density for extremely low R_{DS(ON)}

High power and current handling capability

MAXIMUM RATINGS

Parameter (T _C = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	100V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at T _C = 25°C	I _D	168A
Continuous Drain Current at T _C = 100°C	I _D	119A
Pulsed Drain Current Note 1	I _{DM}	672A
Maximum Power Dissipation at T _C = 25°C	P _D	188W
Power Dissipation Derating above 25°C	ΔP_D	1.25W/°C
Single Pulsed Avalanche Energy Note 4	E _{AS}	684.5mJ
Single Pulsed Avalanche Current Note 4	l _{AS}	37A
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +175°C

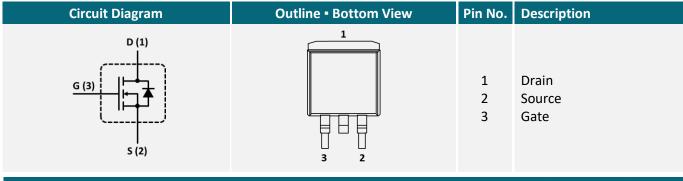
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	0.8°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH JA}	62.5°C/W

APPLICATIONS

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
+ 4 -	50			

PIN DESCRIPTION





ELECTRICAL CHARACTERISTICS ▲ T_C = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit		
Off Characteristics								
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 250\mu A$	BV_DSS	100			V		
Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	I _{DSS}			1	μΑ		
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I_{GSSF}			100	nA		
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I_{GSSR}			-100	nA		
On Characteristics Note 3								
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	$V_{GS(th)}$	2		4	V		
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 20A$	R _{DS(ON)}		3.1	3.7	mΩ		
Dynamic Characteristics Note 3								
Input Capacitance	$V_{DS} = 50V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		3230		pF		
Output Capacitance	$V_{DS} = 50V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		895		pF		
Reverse Transfer Capacitance	$V_{DS} = 50V$, $V_{GS} = 0V$, $f = 1MHz$	C_{RSS}		45		pF		
Switching Characteristics Note 3								
Turn-On Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_D = 20A, $R_{G(ext)}$ = 10 Ω	t _{D(ON)}		38		ns		
Turn-On Rise Time	V_{DD} = 50V, V_{GS} = 10V, I_D = 20A, $R_{G(ext)}$ = 10 Ω	t_R		30		ns		
Turn-Off Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_D = 20A, $R_{G(ext)}$ = 10 Ω	t _{D(OFF)}		86		ns		
Turn-Off Fall Time	V_{DD} = 50V, V_{GS} = 10V, I_D = 20A, $R_{G(ext)}$ = 10 Ω	t _F		61		ns		
Total Gate Charge	$V_{DD} = 50V$, $V_{GS} = 10V$, $I_D = 20A$	Q_{G}		88		nC		
Gate Source Charge	$V_{DD} = 50V$, $V_{GS} = 10V$, $I_D = 20A$	Q_{GS}		17		nC		
Gate Drain Charge	$V_{DD} = 50V$, $V_{GS} = 10V$, $I_D = 20A$	Q_{GD}		31		nC		
Drain-Source Diode Characteristics a	Drain-Source Diode Characteristics and Maximum Ratings							
Drain-Source Diode Forward Current		Is			125	Α		
Drain-Source Diode Forward Voltage Note 2	$V_{GS} = 0V$, $I_S = 10A$	V_{SD}			1.5	V		

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: L = 1mH, I_{AS} = 37A, V_{DD} = 50V, R_{G} = 25Ω, Starting T_{J} = 25°C



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



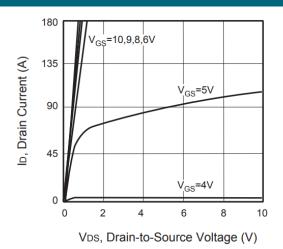


Fig. 2 • Transfer Characteristics

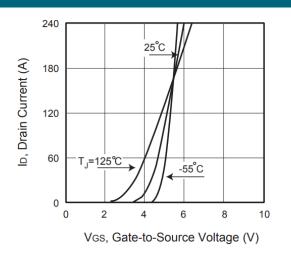


Fig. 3 • Capacitance

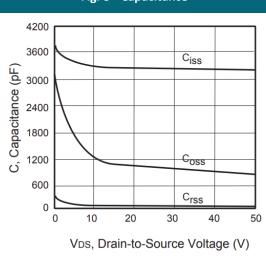


Fig. 4 • On-Resistance Variation with Temperature

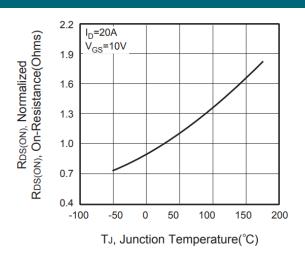


Fig. 5 • Gate Threshold Variation with Temperature

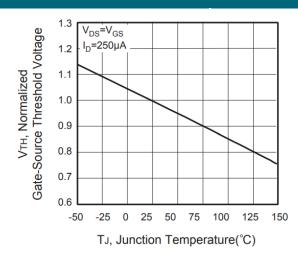
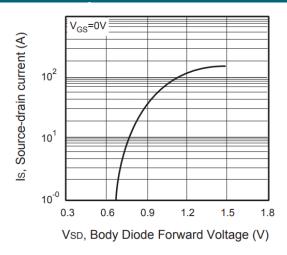


Fig. 6 • Body Diode Forward Voltage Variation with Source Current





REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

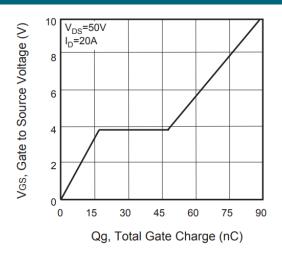


Fig. 8 • Maximum Safe Operating Area

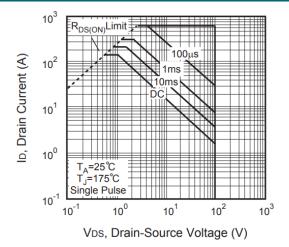
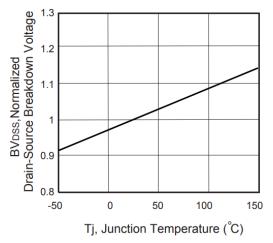


Fig. 9 - Breakdown Voltage Variation vs. Temperature





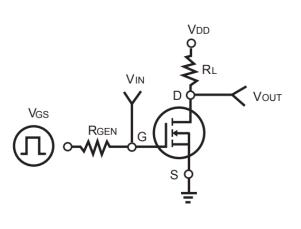
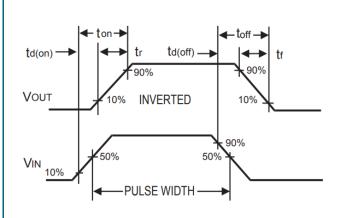


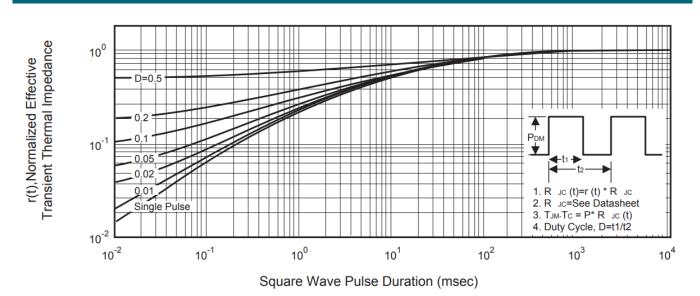
Fig. 11 • Switching Waveforms



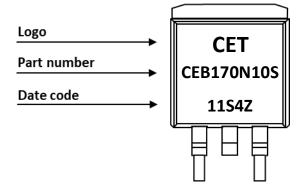


REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 12 • Normalized Thermal Transient Impedance Curve

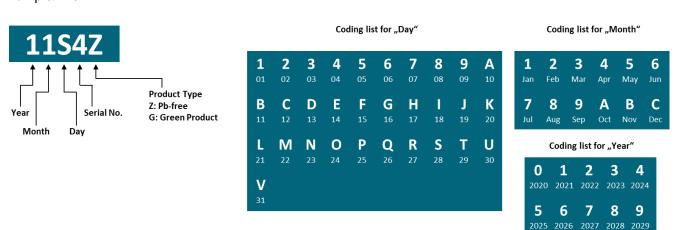


PART MARKING



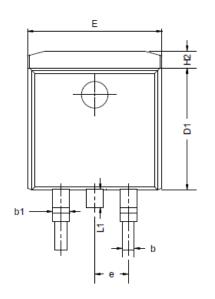
DATE CODE

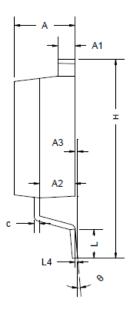
Example: 11S4Z

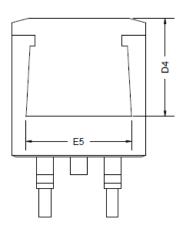


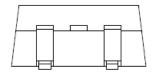


PACKAGE OUTLINE









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
Α	4.37	4.57	4.77	
A1	1.22	1.27	1.42	
A2	2.49	2.69	2.89	
A3	0.00	0.13	0.25	
b	0.70	0.81	0.96	
b1	1.17	1.27	1.47	
С	0.30	0.38	0.53	
D1	8.50	8.70	8.90	
D4	6.60	-	-	

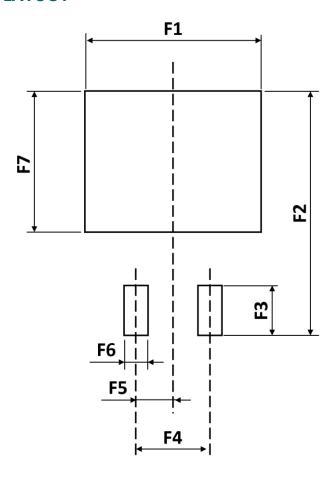
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)			
Е	9.86	10.16	10.36			
E5	7.06	-	-			
е	2.54 BSC					
Н	H 14.70 15.10		15.50			
H2	1.07 1.27		1.47			
L	2.00	2.30	2.60			
L1	1.40	1.55	1.70			
L4	0.25 BSC					
θ	0°	5°	9°			

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CFB170N10S	TO263 (D2PAK)	Reel	800pcs	800ncs	6.400ncs



RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)		
F1	-	12.20	-		
F2	-	16.90	-		
F3	-	2.54	-		
F4	-	5.08	-		

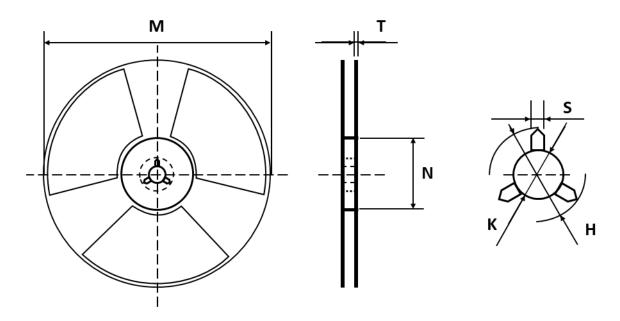
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	2.54	-
F6	-	1.60	-
F7	-	9.75	-

Notes:

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

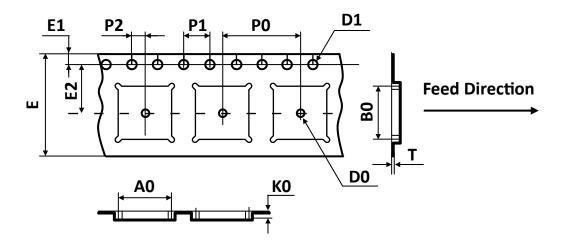


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm	Ø330	±2.00	±0.50	±0.20	+0.50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

TAPE DIMENSIONS ▲ All dimensions in mm

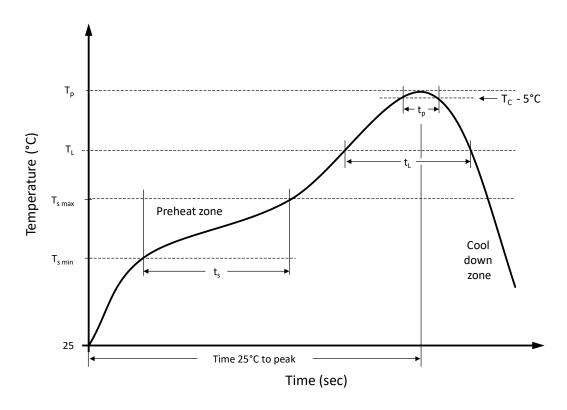


Pac	ckage	Α0	В0	КО	D0	D1	E	E1	E2	Р0	P1	P2	Т
TC	0263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D ²	² PAK)	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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